Transys Electronics LIMITED

SOT-363 Plastic-Encapsulated Diode

SOT-363

BAW56DW SWITCHING DIODE

FEATURES

Power dissipation

P_D: 200 mW (Tamb=25℃)

Collector current

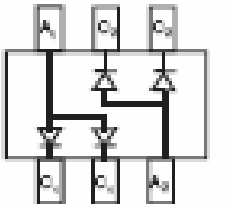
I_F: 150 mA

Collector-base voltage

V_R: 75 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃



MAKING: KJC

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	I_R= 2.5μA	75		V
Reverse voltage leakage current	I_R	V_R=75V V_R=20V		2.5 0.025	μA
Forward voltage	V_F	I_F=1mA I_F=10mA I_F=50mA I_F=150mA		715 855 1000 1250	mV
Junction capacitance	C_j	V_R=0V, f=1MHz		2	pF
Reveres recovery time	t_{rr}	I_F=I_R=10mA I_{rr}=0.1×I_R R_L=100Ω		4	nS

Typical Characteristics

BAW56DW

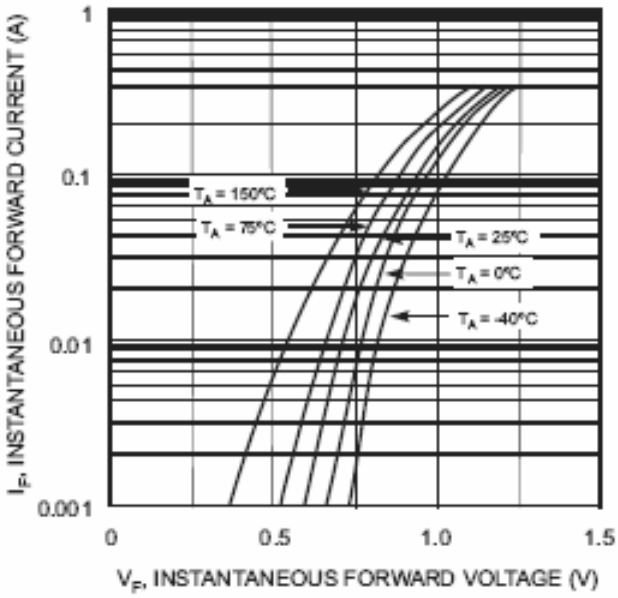


Fig. 1 Forward Characteristics

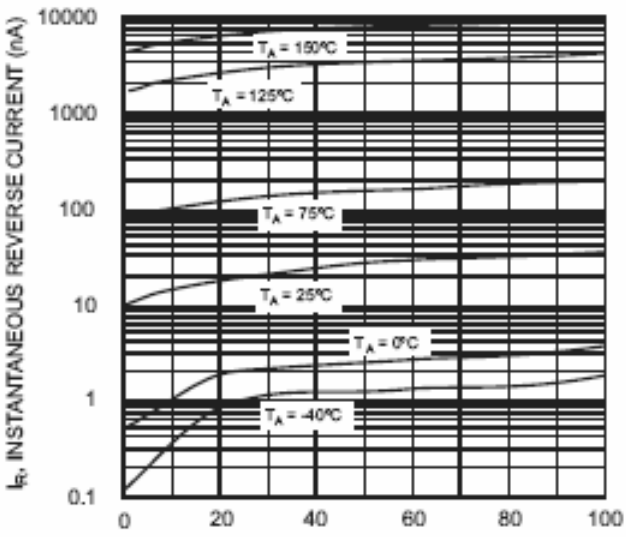


Fig. 2 Typical Reverse Characteristics

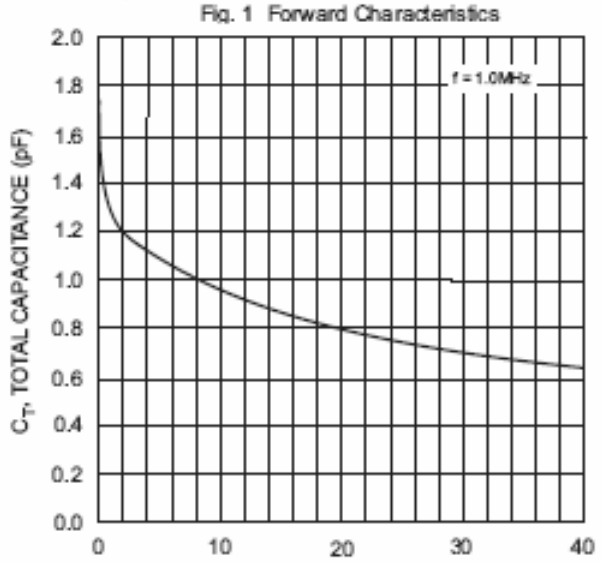


Fig. 3 Typical Capacitance vs. Reverse Voltage

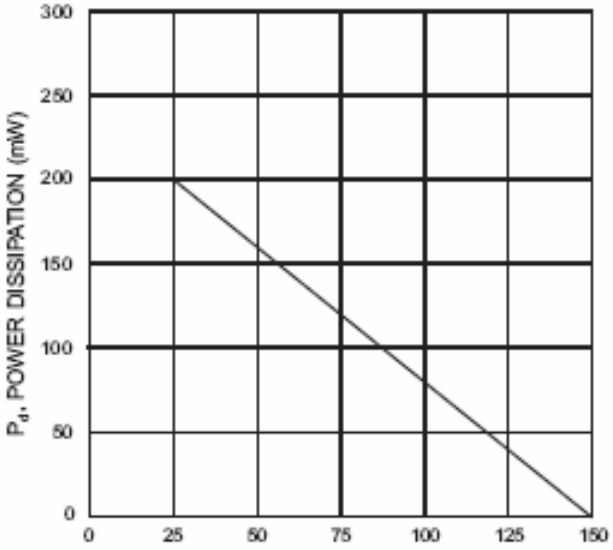


Fig. 4 Power Derating Curve